

# Robert F Davis

## List of Publications by Year in descending order

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449  
papers

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11235

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454  
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454  
docs citations

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times ranked

11488  
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#	ARTICLE	IF	CITATIONS
1	Layered phase composition and microstructure of $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> -dominant heteroepitaxial films grown via MOCVD. Journal of Applied Physics, 2022, 131, .	1.1	12
2	Flow-modulated deposition of sp <sup>2</sup> -boron nitride using diborane and ammonia on chemomechanically polished (0001) 4H-SiC substrates. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 023409.	0.9	1
3	Chemical vapor deposition of sp <sup>2</sup> -boron nitride on mechanically polished pyrolytic boron nitride substrates. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 042203.	0.9	0
4	On the discrepancies between the experimental realization and the thermodynamic predictions of stability of rhombohedral boron nitride. MRS Communications, 2021, 11, 451-456.	0.8	0
5	Progression of central nervous system disease from pediatric to young adulthood in sickle cell anemia. Experimental Biology and Medicine, 2021, 246, 2473-2479.	1.1	4
6	Thermodynamic calculations for the chemical vapor deposition of hexagonal boron nitride using triethylboron, ammonia, and hydrogen. Journal of Crystal Growth, 2021, 572, 126283.	0.7	3
7	Characterization of Epitaxial $\hat{\Gamma}^2$ -(Al,Ga,In) <sub>2</sub> O <sub>3</sub> -Based Films and Applications as UV Photodetectors. Journal of Electronic Materials, 2020, 49, 3490-3498.	1.0	15
8	Metal Organic Chemical Vapor Deposition 2. Springer Series in Materials Science, 2020, , 171-184.	0.4	0
9	Nondiffusive electron transport in metals: A two-temperature Boltzmann transport equation analysis of thermoreflectance experiments. Physical Review B, 2019, 99, .	1.1	1
10	Progression of Central Nervous System Vasculopathy in Young Adults with Sickle Cell Anemia. Blood, 2019, 134, 2290-2290.	0.6	0
11	Growth and characterization of $\langle i \rangle \hat{\Gamma}^{\pm} \langle /i \rangle$ -, $\langle i \rangle \hat{\Gamma}^2 \langle /i \rangle$ -, and $\langle i \rangle \hat{\Gamma}^{\mu} \langle /i \rangle$ -phases of Ga <sub>2</sub> O <sub>3</sub> using MOCVD and HVPE techniques. Materials Research Letters, 2018, 6, 268-275.	4.1	163
12	Electrical behavior of $\langle i \rangle \hat{\Gamma}^2 \langle /i \rangle$ -Ga <sub>2</sub> O <sub>3</sub> Schottky diodes with different Schottky metals. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	0.6	115
13	Investigation of Different Metals as Ohmic Contacts to $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> : Comparison and Analysis of Electrical Behavior, Morphology, and Other Physical Properties. Journal of Electronic Materials, 2017, 46, 2053-2060.	1.0	96
14	(Invited) Growth and Characterization of $\langle i \rangle \hat{\Gamma}^{\pm} \langle /i \rangle$ -, $\langle i \rangle \hat{\Gamma}^2 \langle /i \rangle$ -, and $\langle i \rangle \hat{\Gamma}^{\mu} \langle /i \rangle$ -Ga <sub>2</sub> O <sub>3</sub> Epitaxial Layers on Sapphire. ECS Transactions, 2017, 80, 191-196.	0.3	28
15	Organometallic Vapor Phase Epitaxial Growth of Group III Nitrides $\hat{\Gamma}^{\pm}$ . , 2017, , .		0
16	(Invited) Growth and Characterization of $\hat{\Gamma}^{\pm}$ -, $\hat{\Gamma}^2$ -, and $\hat{\Gamma}^{\mu}$ -Ga <sub>2</sub> O <sub>3</sub> Epitaxial Layers on Sapphire. ECS Meeting Abstracts, 2017, , .	0.0	0
17	Polymer ligand-induced autonomous sorting and reversible phase separation in binary particle blends. Science Advances, 2016, 2, e1601484.	4.7	30
18	Thermal interface conductance across metal alloy-dielectric interfaces. Physical Review B, 2016, 93, .	1.1	20

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19	Analysis of compositional uniformity in Al <sub>x</sub> Ga <sub>1-x</sub> N thin films using atom probe tomography and electron microscopy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016, 34, .	0.9	5
20	Substrates and epitaxial deposition processes for Group III-nitride thin films and power device heterostructures. <i>MRS Bulletin</i> , 2015, 40, 406-411.	1.7	1
21	Photoemission investigation of the Schottky barrier at the Sc/3C-SiC (111) interface. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 391-396.	0.7	11
22	Hydrogen desorption from hydrogen fluoride and remote hydrogen plasma cleaned silicon carbide (0001) surfaces. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015, 33, .	0.9	7
23	Cleaning of pyrolytic hexagonal boron nitride surfaces. <i>Surface and Interface Analysis</i> , 2015, 47, 798-803.	0.8	10
24	Band alignment at AlN/Si (111) and (001) interfaces. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	8
25	Hydrogen desorption kinetics for aqueous hydrogen fluoride and remote hydrogen plasma processed silicon (001) surfaces. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015, 33, .	0.9	6
26	Valence and conduction band alignment at ScN interfaces with 3C-SiC (111) and 2H-GaN (0001). <i>Applied Physics Letters</i> , 2014, 105, 081606.	1.5	14
27	Desorption and sublimation kinetics for fluorinated aluminum nitride surfaces. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2014, 32, .	0.9	9
28	Site-specific comparisons of V-defects and threading dislocations in InGaN/GaN multi-quantum-wells grown on SiC and GaN substrates. <i>Journal of Crystal Growth</i> , 2014, 387, 16-22.	0.7	12
29	Gas source molecular beam epitaxy of scandium nitride on silicon carbide and gallium nitride surfaces. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2014, 32, .	0.9	38
30	Composition and interface analysis of InGaN/GaN multiquantum-wells on GaN substrates using atom probe tomography. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014, 32, 051209.	0.6	10
31	Rugged Electrical Power Switching in Semiconductors: A Systems Approach. <i>Proceedings of the IEEE</i> , 2014, 102, 35-52.	16.4	16
32	Universal phonon mean free path spectra in crystalline semiconductors at high temperature. <i>Scientific Reports</i> , 2013, 3, 2963.	1.6	125
33	Modeling the Electrical Response of Hydrogen Sensors Based on AlGaIn/GaN High-Electron-Mobility Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2013, 2, Q214-Q219.	0.9	3
34	The impact of film thickness and substrate surface roughness on the thermal resistance of aluminum nitride nucleation layers. <i>Journal of Applied Physics</i> , 2013, 113, .	1.1	30
35	Current Status and Emerging Trends in Wide Bandgap (WBG) Semiconductor Power Switching Devices. <i>ECS Journal of Solid State Science and Technology</i> , 2013, 2, N3055-N3063.	0.9	54
36	Dislocations as quantum wires: Buffer leakage in AlGaIn/GaN heterostructures. <i>Journal of Materials Research</i> , 2013, 28, 1687-1691.	1.2	9

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37	Material Defects and Rugged Electrical Power Switching in Semiconductors. Materials Science Forum, 2012, 717-720, 1077-1080.	0.3	2
38	Layer-by-layer thermal conductivities of the Group III nitride films in blue/green light emitting diodes. Applied Physics Letters, 2012, 100, .	1.5	43
39	Impact of Solid State Lighting on Energy Utilization and Environmental Conditions. Transactions of the Materials Research Society of Japan, 2012, 20thAnniv, 41-45.	0.2	0
40	Microstructure of epitaxial GaN films grown on chemomechanically polished GaN(0001) substrates. Journal of Crystal Growth, 2012, 347, 88-94.	0.7	17
41	Identifying threading dislocations in GaN films and substrates by electron channelling. Journal of Microscopy, 2011, 244, 311-319.	0.8	14
42	Green Emission of Silicon Quantum Dot Light-emitting Diodes caused by Enhanced Carrier Injection. Journal of the Korean Physical Society, 2011, 59, 2183-2186.	0.3	2
43	Optical property of silicon quantum dots embedded in silicon nitride by thermal annealing. Thin Solid Films, 2010, 518, 1744-1746.	0.8	9
44	Surface and defect microstructure of GaN and AlN layers grown on hydrogen-etched 6H-SiC(0001) substrates. Acta Materialia, 2010, 58, 2165-2175.	3.8	24
45	Impact of Solid State Lighting on Energy Utilization and Environmental Conditions. Transactions of the Materials Research Society of Japan, 2010, 35, 467-471.	0.2	0
46	Enhancement of Electrical and Optical Properties of Silicon Quantum Dot Light-Emitting Diodes with ZnO Doping Layer. Japanese Journal of Applied Physics, 2009, 48, 105004.	0.8	0
47	Enhanced performance of silicon quantum dot light-emitting diodes grown on nanoroughened silicon substrate. Applied Physics Letters, 2009, 95, 073113.	1.5	14
48	Hydrogen desorption kinetics and band bending for 6H-SiC(0001) surfaces. Surface Science, 2009, 603, 3104-3118.	0.8	27
49	On the origin of aluminum-related cathodoluminescence emissions from sublimation grown 4H-SiC(). Applied Surface Science, 2009, 255, 6535-6539.	3.1	6
50	Sequential growths of AlN and GaN layers on as-polished 6H-SiC(0001) substrates. Acta Materialia, 2009, 57, 4001-4008.	3.8	21
51	Effect of injection current density on electroluminescence in silicon quantum dot light-emitting diodes. Applied Physics Letters, 2009, 95, 153103.	1.5	5
52	Kinetics of Ga and In desorption from (7 $\times$ 7) Si(111) and (3 $\times$ 3) 6H-SiC(0001) surfaces. Surface Science, 2008, 602, 405-415.	0.8	13
53	Sublimation growth of an in-situ-deposited layer in SiC chemical vapor deposition on 4H-SiC(112 $\bar{0}$ ). Journal of Crystal Growth, 2008, 311, 72-78.	0.7	3
54	Phonon-assisted stimulated emission from pendeoepitaxy GaN stripes grown on 6H-SiC substrates. Applied Physics Letters, 2007, 91, 051119.	1.5	3

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55	Electrical and optical properties of ZnO (0001 $\hat{\wedge}$ ) wafers implanted with argon. Journal of Applied Physics, 2007, 101, 024902.	1.1	5
56	Growth evolution and pendeo-epitaxy of non-polar AlN and GaN thin films on 4H $\hat{\wedge}$ SiC (112 $\hat{\wedge}$ 0). Journal of Crystal Growth, 2007, 300, 83-89.	0.7	10
57	Characterization of growth defects in thin GaN layers with X-ray microbeam. Physica Status Solidi (B): Basic Research, 2007, 244, 1735-1742.	0.7	6
58	Polytype Stability and Microstructural Characterization of Silicon Carbide Epitaxial Films Grown on [ $\overline{111}$ ]- and [0001]-Oriented Silicon Carbide Substrates. Journal of Electronic Materials, 2007, 36, 285-296.	1.0	6
59	Effect of thermal annealing on the metastable optical properties of GaN thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 1051-1054.	0.9	1
60	Ohmic Contacts to GaN. , 2006, , 489-527.		0
61	Mapping misorientation and crystallographic tilt in GaN layers via polychromatic microdiffraction. Physica Status Solidi (B): Basic Research, 2006, 243, 1508-1513.	0.7	1
62	Optimization of a Nanoparticle Suspension for Freeze Casting. Journal of the American Ceramic Society, 2006, 89, 2459-2465.	1.9	64
63	Growth and characterization of pendeo-epitaxial GaN on 4H $\hat{\wedge}$ SiC substrates. Journal of Crystal Growth, 2006, 290, 504-512.	0.7	16
64	Growth and structural investigations of epitaxial hexagonal YMnO3 thin films deposited on wurtzite GaN(001) substrates. Thin Solid Films, 2006, 515, 1807-1813.	0.8	17
65	Growth and fabrication of AlGaIn-based ultraviolet light emitting diodes on 6H-SiC(0001) substrates and the effect of carrier-blocking layers on their emission characteristics. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 127, 169-179.	1.7	4
66	Origins of Parasitic Emissions from 353 nm AlGaIn-based Ultraviolet Light Emitting Diodes over SiC Substrates. Japanese Journal of Applied Physics, 2006, 45, 4083-4086.	0.8	17
67	Photo-electron emission and atomic force microscopies of the hydrogen etched 6H-SiC(0001) surface and the initial growth of GaN and AlN. Applied Surface Science, 2005, 242, 428-436.	3.1	6
68	Growth of dense ZnO films via MOVPE on GaN(0001) epilayers using a low/high-temperature sequence. Journal of Crystal Growth, 2005, 277, 345-351.	0.7	12
69	Heteroepitaxial growth of dense ZnO(0001) and ZnO $\langle 111 \rangle$ films on GaN(0001) substrates. Journal of Crystal Growth, 2005, 277, 345-351. <a href="http://www.elsevier.com/xml/xocs/dtd">http://www.elsevier.com/xml/xocs/dtd</a> <a href="http://www.w3.org/2001/XMLSchema">xmlns:xs="http://www.w3.org/2001/XMLSchema"</a> <a href="http://www.w3.org/2001/XMLSchema-instance">xmlns:xsi="http://www.w3.org/2001/XMLSchema-instance"</a> <a href="http://www.elsevier.com/xml/ja/dtd">xmlns="http://www.elsevier.com/xml/ja/dtd"</a> <a href="http://www.w3.org/1998/Math/MathML">xmlns:ja="http://www.elsevier.com/xml/ja/dtd"</a> <a href="http://www.w3.org/1998/Math/MathML">xmlns:mml="http://www.w3.org/1998/Math/MathML"</a> <a href="http://www.elsevier.com/xml/common/table/dtd">xmlns:tb="http://www.elsevier.com/xml/common/table/dtd"</a> <a href="http://www.elsevier.com/xml/common/struct-bib/dtd">xmlns:sb="http://www.elsevier.com/xml/common/struct-bib/dtd"</a> <a href="http://www.elsevier.com/xml/common/struct-bib/dtd">xmlns:ce="http://www.elsevier.com/xml/common/struct-bib/dtd"</a> <a href="http://www.elsevier.com/xml/common/struct-bib/dtd">xmlns:ce="http://www.elsevier.com/xml/common/struct-bib/dtd"</a> Journal of Crystal Growth, 2005, 277, 345-351.	0.7	21
70	P-type doping utilizing nitrogen and Mn doping of ZnO using MOCVD for ultraviolet lasers and spintronic applications. Journal of Electronic Materials, 2005, 34, 949-952.	1.0	15
71	The formation of epitaxial hexagonal boron nitride on nickel substrates. Journal of Electronic Materials, 2005, 34, 1558-1564.	1.0	18
72	The effects of oxygen, nitrogen, and hydrogen annealing on Mg acceptors in GaN as monitored by electron paramagnetic resonance spectroscopy. Journal of Electronic Materials, 2005, 34, 34-39.	1.0	14

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73	Comparison of the microstructure and chemistry of GaN(0001) films grown using trimethylgallium and triethylgallium on AlN/SiC substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 2166-2169.	0.8	1
74	White X-ray microbeam analysis of strain and crystallographic tilt in GaN layers grown by maskless pendeoepitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 732-738.	0.8	8
75	A Printable Form of Single-Crystalline Gallium Nitride for Flexible Optoelectronic Systems. <i>Small</i> , 2005, 1, 1164-1168.	5.2	109
76	On the microstructure of Al <sub>x</sub> Ga <sub>1-x</sub> N layers grown on 6H-SiC(0001) substrates. <i>Journal of Applied Physics</i> , 2005, 97, 083501.	1.1	8
77	Preparation and characterization of atomically clean, stoichiometric surfaces of AlN(0001). <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2005, 23, 72-77.	0.9	8
78	Local strain, defects, and crystallographic tilt in GaN(0001) layers grown by maskless pendeo-epitaxy from x-ray microdiffraction. <i>Journal of Applied Physics</i> , 2005, 97, 013504.	1.1	9
79	Origins of Parasitic Emissions from 353 nm AlGaIn-based UV LEDs over SiC Substrates. <i>Materials Research Society Symposia Proceedings</i> , 2005, 892, 154.	0.1	0
80	Structural TEM study of nonpolar a-plane gallium nitride grown on (112̄0)4H-SiC by organometallic vapor phase epitaxy. <i>Physical Review B</i> , 2005, 71, .	1.1	193
81	Step-Controlled Strain Relaxation in the Vicinal Surface Epitaxy of Nitrides. <i>Physical Review Letters</i> , 2005, 95, 086101.	2.9	51
82	Intersecting basal plane and prismatic stacking fault structures and their formation mechanisms in GaN. <i>Journal of Applied Physics</i> , 2005, 98, 063510.	1.1	19
83	Structural defects and luminescence features in heteroepitaxial GaN grown on on-axis and misoriented substrates. <i>Journal of Applied Physics</i> , 2005, 97, 116101.	1.1	16
84	Structural, microstructural, and electrical properties of gold films and Schottky contacts on remote plasma-cleaned, n-type ZnO{0001} surfaces. <i>Journal of Applied Physics</i> , 2005, 97, 103517.	1.1	131
85	Effect of Carrier Blocking Layers on the Emission Characteristics of AlGaIn-based Ultraviolet Light Emitting Diodes. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 7254-7259.	0.8	16
86	In situcleaning of GaN(0001) surfaces in a metalorganic vapor phase epitaxy environment. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004, 22, 2077-2082.	0.9	8
87	In situcleaning and characterization of oxygen- and zinc-terminated, n-type, ZnO{0001} surfaces. <i>Journal of Applied Physics</i> , 2004, 95, 5856-5864.	1.1	84
88	Surface-roughness correlations in homoepitaxial growth of GaN(0001) films by NH <sub>3</sub> supersonic jet epitaxy. <i>Journal of Applied Physics</i> , 2004, 96, 4556-4562.	1.1	3
89	Selective Etching of GaN from AlGaIn/GaN and AlN/GaN Structures. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 2004, 9, 1.	1.0	9
90	Homoepitaxial growth of (0001)- and -oriented ZnO thin films via metalorganic vapor-phase epitaxy and their characterization. <i>Journal of Crystal Growth</i> , 2004, 265, 390-398.	0.7	32

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91	Growth and characterization of ZnO thin films on GaN epilayers. Journal of Electronic Materials, 2004, 33, 826-832.	1.0	7
92	HVPE-GaN: comparison of emission properties and microstructure of films grown on different laterally overgrown templates. Diamond and Related Materials, 2004, 13, 1125-1129.	1.8	7
93	Growth of Homoepitaxial Films on 4H-SiC(11-20) and 8° Off-Axis 4H-SiC(0001) Substrates and their Characterization. Materials Science Forum, 2004, 457-460, 221-224.	0.3	2
94	Gallium nitride and related materials: challenges in materials processing. Acta Materialia, 2003, 51, 5961-5979.	3.8	59
95	Helical-type surface defects in GaN thin films epitaxially grown on GaN templates at reduced temperatures. Journal of Crystal Growth, 2003, 253, 16-25.	0.7	13
96	Surface morphology and strain of GaN layers grown using 6H-SiC(0001) substrates with different buffer layers. Journal of Crystal Growth, 2003, 253, 129-141.	0.7	42
97	Helical-type surface defects in InGaN thin films epitaxially grown on GaN templates at reduced temperatures. Thin Solid Films, 2003, 437, 140-149.	0.8	9
98	Evolution and growth of ZnO thin films on GaN(0001) epilayers via metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2003, 257, 255-262.	0.7	22
99	Domain structures in 6H-SiC wafers and their effect on the microstructures of GaN films grown on AlN and Al <sub>0.2</sub> Ga <sub>0.8</sub> N buffer layers. Journal of Crystal Growth, 2003, 258, 75-83.	0.7	4
100	Electron energy distribution during high-field transport in AlN. Journal of Applied Physics, 2003, 93, 2765-2771.	1.1	5
101	High performance 0.14 μm gate-length AlGaIn/GaN power HEMTs on SiC. IEEE Electron Device Letters, 2003, 24, 677-679.	2.2	15
102	Gold Schottky contacts on oxygen plasma-treated, n-type ZnO(0001). Applied Physics Letters, 2003, 82, 400-402.	1.5	378
103	Growth and Characterization of AlN and GaN Thin Films Deposited on Si(111) Substrates Containing a Very Thin Al Layer. Materials Research Society Symposia Proceedings, 2003, 798, 140.	0.1	0
104	Measurement of the band offsets of SiO <sub>2</sub> on clean- and p-type GaN(0001). Journal of Applied Physics, 2003, 93, 3995-4004.	1.1	83
105	Electrical and chemical characterization of the Schottky barrier formed between clean n-GaN(0001) surfaces and Pt, Au, and Ag. Journal of Applied Physics, 2003, 94, 3939-3948.	1.1	97
106	Supersonic jet epitaxy of gallium nitride using triethylgallium and ammonia. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 294-301.	0.9	3
107	Microscopic mapping of strain relaxation in uncoalesced pseudoepitaxial GaN on SiC. Physical Review B, 2003, 67, .	1.1	17
108	Band offset measurements of the GaN(0001)/HfO <sub>2</sub> interface. Journal of Applied Physics, 2003, 94, 7155-7158.	1.1	65

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109	Characterization of hydrogen etched 6H-SiC(0001) substrates and subsequently grown AlN films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 394-400.	0.9	15
110	Preparation and characterization of atomically clean, stoichiometric surfaces of n- and p-type GaN(0001). Journal of Applied Physics, 2003, 94, 3163-3172.	1.1	111
111	Band offset measurements of the Si <sub>3</sub> N <sub>4</sub> /GaN(0001) interface. Journal of Applied Physics, 2003, 94, 3949-3954.	1.1	82
112	Response to Comment on "Pd growth and subsequent Schottky barrier formation on chemical vapor cleaned p-type GaN surfaces" [J. Appl. Phys. 91, 732 (2002)]. Journal of Applied Physics, 2003, 93, 3679-3679.	1.1	0
113	Electron-beam-induced optical memory effects in GaN. Applied Physics Letters, 2002, 80, 2675-2677.	1.5	14
114	Cross-sectional imaging of pendeo-epitaxial GaN using continuous-wave two-photon microphotoluminescence. Applied Physics Letters, 2002, 81, 1984-1986.	1.5	9
115	Chemical, electrical, and structural properties of Ni/Au contacts on chemical vapor cleaned p-type GaN. Journal of Applied Physics, 2002, 91, 9151-9160.	1.1	24
116	Pd growth and subsequent Schottky barrier formation on chemical vapor cleaned p-type GaN surfaces. Journal of Applied Physics, 2002, 91, 732-738.	1.1	37
117	Electrical, structural and microstructural characteristics of as-deposited and annealed Pt and Au contacts on chemical-vapor-cleaned GaN thin films. Journal of Applied Physics, 2002, 91, 2133-2137.	1.1	10
118	Probing the Al <sub>x</sub> Ga <sub>1-x</sub> N spatial alloy fluctuation via UV-photoluminescence and Raman at submicron scale. Applied Physics Letters, 2002, 81, 4186-4188.	1.5	10
119	Strain and crystallographic tilt in uncoalesced GaN layers grown by maskless pendeoepitaxy. Applied Physics Letters, 2002, 80, 953-955.	1.5	39
120	Observations of electron velocity overshoot during high-field transport in AlN. Materials Research Society Symposia Proceedings, 2002, 743, L10.2.1.	0.1	0
121	Probing the Al <sub>x</sub> Ga <sub>1-x</sub> N Atomic Distribution via UV-Photoluminescence and Raman at Sub-1/2μm Scale. Materials Research Society Symposia Proceedings, 2002, 719, 8231.	0.1	0
122	Investigations regarding the maskless pendeo-epitaxial growth of GaN films prior to coalescence. IEEE Journal of Quantum Electronics, 2002, 38, 1006-1016.	1.0	20
123	TiC nanoisland formation on 6H-SiC(0001)Si. Journal of Applied Physics, 2002, 91, 6081-6084.	1.1	0
124	Strain in cracked AlGaIn layers. Journal of Applied Physics, 2002, 92, 118-123.	1.1	30
125	Gallium nitride materials - progress, status, and potential roadblocks. Proceedings of the IEEE, 2002, 90, 993-1005.	16.4	34
126	Effect Of Implantation Temperature On Damage Accumulation In Ar - Implanted GaN. MRS Internet Journal of Nitride Semiconductor Research, 2002, 7, 1.	1.0	5



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127	Maskless pendeo-epitaxial growth of GaN films. Journal of Electronic Materials, 2002, 31, 421-428.	1.0	10
128	Application of Nomarski interference contrast microscopy as a thickness monitor in the preparation of transparent, SiC-based, cross-sectional TEM samples. Ultramicroscopy, 2002, 92, 265-271.	0.8	9
129	The influence of band offsets on the IV characteristics for GaN/SiC heterojunctions. Solid-State Electronics, 2002, 46, 827-835.	0.8	18
130	Growth and decomposition of bulk GaN: role of the ammonia/nitrogen ratio. Journal of Crystal Growth, 2002, 236, 529-537.	0.7	16
131	Surface instability and associated roughness during conventional and pendeo-epitaxial growth of GaN(0001) films via MOVPE. Journal of Crystal Growth, 2002, 241, 141-150.	0.7	35
132	High temperature nucleation and growth of GaN crystals from the vapor phase. Journal of Crystal Growth, 2002, 241, 404-415.	0.7	22
133	Kinetics and gas-surface dynamics of GaN homoepitaxial growth using NH <sub>3</sub> -seeded supersonic molecular beams. Surface Science, 2001, 494, 28-42.	0.8	12
134	Polarization charges and polarization-induced barriers in Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN and In <sub>y</sub> Ga <sub>1-y</sub> N/GaN heterostructures. Applied Physics Letters, 2001, 79, 2916-2918.	1.5	12
135	Reverse-annealing phenomenon during the high-temperature implantation of Ar into GaN. Materials Research Society Symposia Proceedings, 2001, 693, 120.	0.1	2
136	Surface Instability and Associated Roughness of Pendeo-epitaxy GaN (0001) Films Grown via Metalorganic Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 2001, 693, 359.	0.1	0
137	Removal of 6H-SiC substrate influence when evaluating GaN thin film properties via x-ray. Materials Research Society Symposia Proceedings, 2001, 693, 519.	0.1	0
138	Electron transport in AlN under high electric fields. Materials Research Society Symposia Proceedings, 2001, 693, 666.	0.1	0
139	Helical-Type Surface Defects in GaN and InGaN Thin Films Epitaxially Grown on GaN Templates at Reduced Temperatures. Materials Research Society Symposia Proceedings, 2001, 693, 69.	0.1	0
140	Review of Pendeo-Epitaxial Growth and Characterization of Thin Films of GaN and AlGaN Alloys on 6H-SiC(0001) and Si(111) Substrates. MRS Internet Journal of Nitride Semiconductor Research, 2001, 6, 1.	1.0	25
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